



[WeA2] Nanoscale Thin Film Deposition IV

Session Date	November 12 (Wed.), 2025
Session Time	14:10–15:50
Session Room	Room A (Capri Room, 2F)
Session Chair	Prof. Jin-Seong Park (Hanyang Univ., Korea)

[WeA2-1] [Invited]

14:10–14:40

2D Semiconductor Crystal Layer Deposition Toward Fab-Line Compatibility

Kibum Kang (KAIST and TDS Innovation Co., Ltd., Korea)

[WeA2-2] [Invited]

14:40–15:10

Innovations in Deposition Technologies at the Onset of 3D Devices

Kwangmin Park, J.U. Kim, I. Zoh, S.H. Jang, T. Lee, S. Jeong, I. Jeon, Y.S. Tak, S.W. Jung, S.Y. Yang, H.J. Kim, Z. Wu, S.C. Oh, J.H. Park, S.U. Han, M.H. Cho, Y. Kim, P. Yun, J.W. Han, S.W. Park, Daewon Ha, S.H. Lee, S.J. Ahn, S.J. Hyun, and Jaihyuk Song (Samsung Electronics Co., Ltd., Korea)

[WeA2-3] [Invited]

15:10–15:30

ALD/ALE for the Advanced Technology

Van Quang Nguyen, Minji Jeong, Dohoe Kim, and Jihye Kim (ISAC Research Inc., Korea)

[WeA2-4]

15:30–15:50

Development of ALD-Based Initial Surface Control Technology for Sub-10 nm Continuous Ir Films in Advanced Interconnect Metallization

Myung-Jin Jung and Se-Hun Kwon (Pusan Nat'l Univ., Korea)